

L3 ANSWER 12 OF 12 CAPLUS COPYRIGHT 2002 ACS
AB In forming a **SOG** film by coating a no. of **SOG** layers during the fabrication of a semiconductor device, the surface of a **SOG** layer is treated with a plasma prior to applying an addnl. layer to improve the bonding between **SOG** layers. Specifically, a gas contg. Ar, Kr, Ne, Xe, N2, and/or He may be used for the plasma treatment.
ST semiconductor device fabrication **SOG** plasma treatment
IT Coating process
Plasma
Semiconductor device fabrication
(plasma treatment of **SOG** layers in semiconductor device fabrication)
IT Glass, processes
RL: DEV (Device component use); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)
(spin on; plasma treatment of **SOG** layers in semiconductor device fabrication)
IT 7439-90-9, Krypton, uses 7440-01-9, Neon, uses 7440-37-1, **Argon**, uses 7440-59-7, Helium, uses 7440-63-3, Xenon, uses 7727-37-9, Nitrogen, uses
RL: NUU (Other use, unclassified); USES (Uses)
(in **plasma treatment** of **SOG** layers in semiconductor device fabrication)
AN 1999:387926 CAPLUS
DN 131:26608
TI Production method of semiconductor device.
IN Yasuhara, Masanori
PA Seiko Epson Corp., Japan
SO Jpn. Kokai Tokkyo Koho, 4 pp.
CODEN: JKXXAF